

## Silicon PNP Power Transistors

2SA1180

**DESCRIPTION**

- With TO-3 package
- High power dissipations

**APPLICATIONS**

- For power switching amplifier and general purpose applications

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

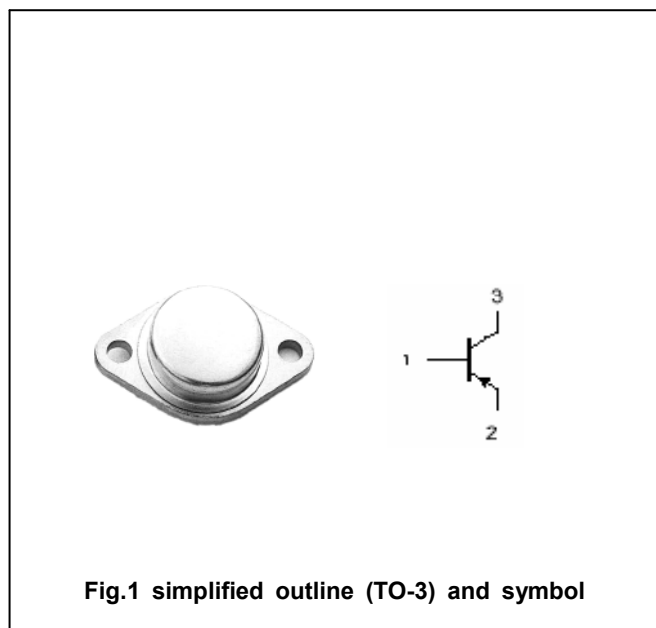


Fig.1 simplified outline (TO-3) and symbol

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-180	V
$V_{CEO}$	Collector-emitter voltage	Open base	-180	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-10	A
$I_B$	Base current		-4	A
$P_C$	Collector power dissipation	$T_C=25^\circ$	100	W
$T_j$	Junction temperature		150	□
$T_{stg}$	Storage temperature		-55~150	□

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA ; I <sub>B</sub> =0	-180			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-1mA ; I <sub>E</sub> =0	-180			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA ; I <sub>C</sub> =0	-6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A; I <sub>B</sub> =-0.5A			-2.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-180V; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-4V	30			

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)